

# FDD6670S

## 30V N-Channel PowerTrench<sup>®</sup> SyncFET™

### General Description

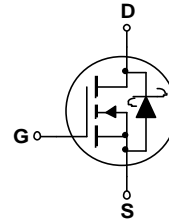
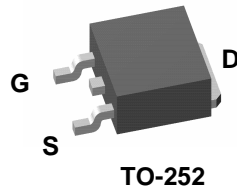
The FDD6670S is designed to replace a single MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. The FDD6670S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology. The performance of the FDD6670S as the low-side switch in a synchronous rectifier is indistinguishable from the performance of the FDD6670A in parallel with a Schottky diode.

### Applications

- DC/DC converter
- Motor Drives

### Features

- 64 A, 30 V  $R_{DS(ON)} = 9 \text{ m}\Omega$  @  $V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 12.5 \text{ m}\Omega$  @  $V_{GS} = 4.5 \text{ V}$
- Includes SyncFET Schottky body diode
- Low gate charge (17nC typical)
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability



### Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous (Note 3)	64	A
	– Pulsed (Note 1a)	100	
$P_D$	Power Dissipation (Note 1) (Note 1a) (Note 1b)	70	W
		3.2	
		1.3	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	$-55$ to $+150$	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	1.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD6670S	FDD6670S	13"	16mm	2500 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Drain-Source Avalanche Ratings** (Note 2)

$W_{DSS}$	Drain-Source Avalanche Energy	Single Pulse, $V_{DD} = 15\text{ V}$ , $I_D = 14\text{ A}$			245	mJ
$I_{AR}$	Drain-Source Avalanche Current				14	A

**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$		19		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$			500	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -20\text{ V}$ , $V_{DS} = 0\text{ V}$			-100	nA

**On Characteristics** (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 1\text{ mA}$	1	2	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$		-3.3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 13.8\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 11.7\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 13.8\text{ A}$ , $T_J = 125^\circ\text{C}$		6 9 10	9 12.5 15	m $\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 5\text{ V}$	50			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 15\text{ V}$ , $I_D = 13.8\text{ A}$		27		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		2010		pF
$C_{oss}$	Output Capacitance			526		pF
$C_{rss}$	Reverse Transfer Capacitance			186		pF

**Switching Characteristics** (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 15\text{ V}$ , $I_D = 1\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		10	18	ns
$t_r$	Turn-On Rise Time			10	18	ns
$t_{d(off)}$	Turn-Off Delay Time			34	55	ns
$t_f$	Turn-Off Fall Time			14	23	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}$ , $I_D = 13.8\text{ A}$ , $V_{GS} = 10\text{ V}$		17	24	nC
$Q_{gs}$	Gate-Source Charge			6.2		nC
$Q_{gd}$	Gate-Drain Charge			5.5		nC

**Drain-Source Diode Characteristics**

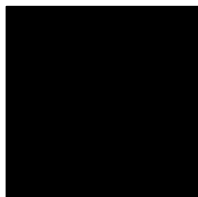
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 3.5\text{ A}$ (Note 2) $V_{GS} = 0\text{ V}$ , $I_S = 7\text{ A}$ (Note 2)		0.49 0.56	0.7	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 3.5\text{ A}$ , $dI_F/dt = 300\text{ A}/\mu\text{s}$ (Note 3)		20		nS
$Q_{rr}$	Diode Reverse Recovery Charge			19.7		nC

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

### Notes:

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



- a)  $R_{\theta JA} = 40^\circ\text{C/W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper



- b)  $R_{\theta JA} = 96^\circ\text{C/W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width <  $300\mu\text{s}$ , Duty Cycle < 2.0%

3. Maximum current is calculated as:  $\sqrt{\frac{P_D}{R_{DS(ON)}}}$

where  $P_D$  is maximum power dissipation at  $T_C = 25^\circ\text{C}$  and  $R_{DS(on)}$  is at  $T_{J(max)}$  and  $V_{GS} = 10\text{V}$ . Package current limitation is 21A

# Typical Characteristics

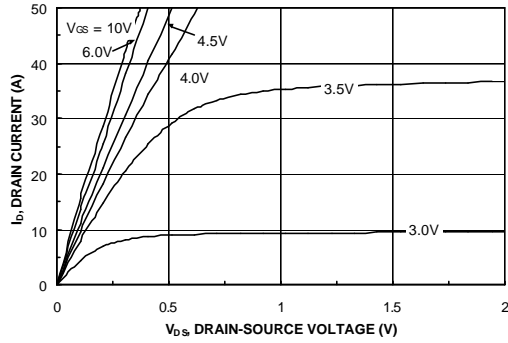


Figure 1. On-Region Characteristics.

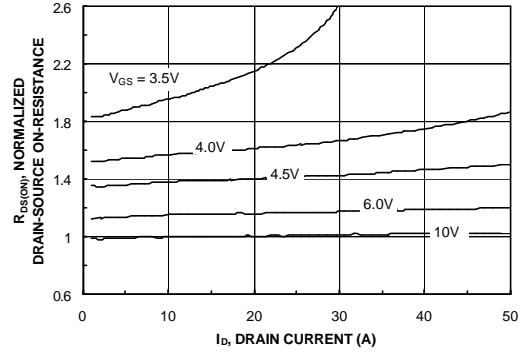


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

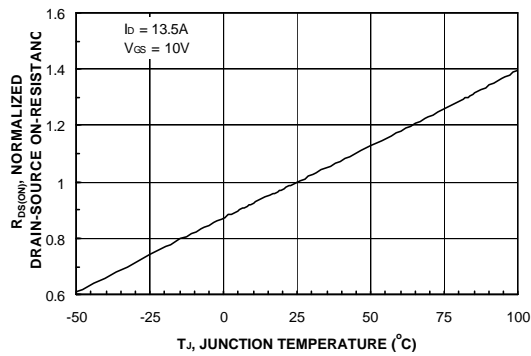


Figure 3. On-Resistance Variation with Temperature.

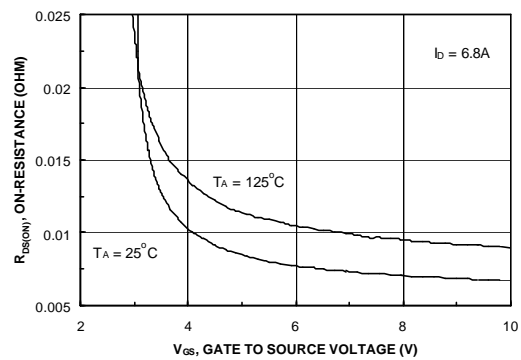


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

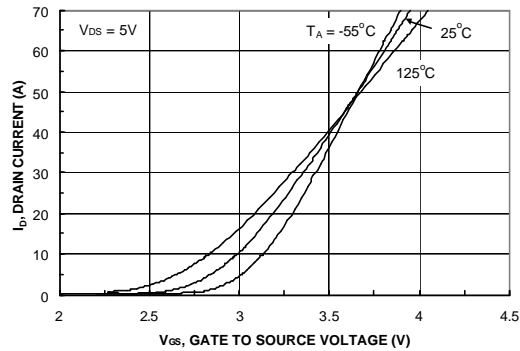


Figure 5. Transfer Characteristics.

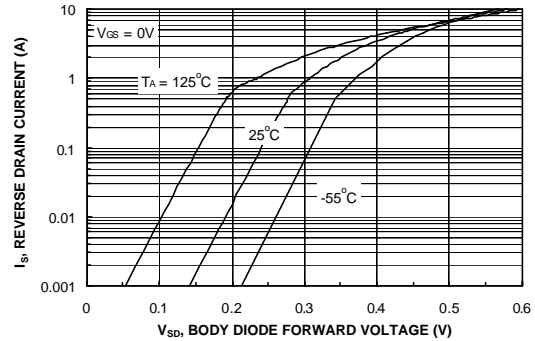


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# Typical Characteristics (continued)

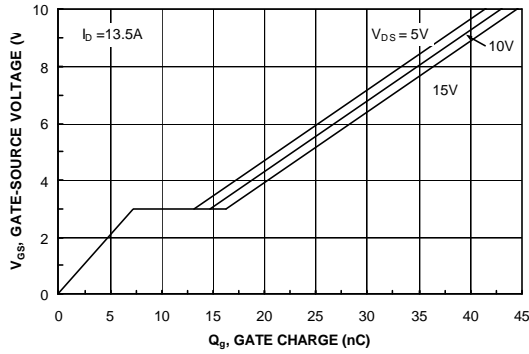


Figure 7. Gate Charge Characteristics.

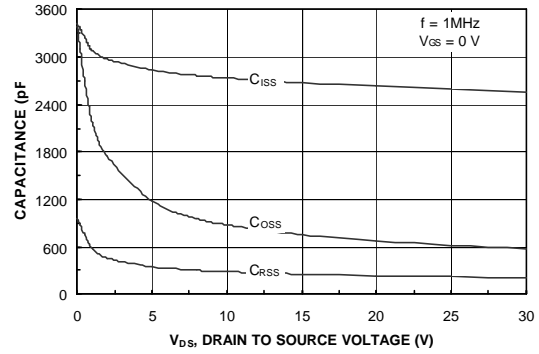


Figure 8. Capacitance Characteristics.

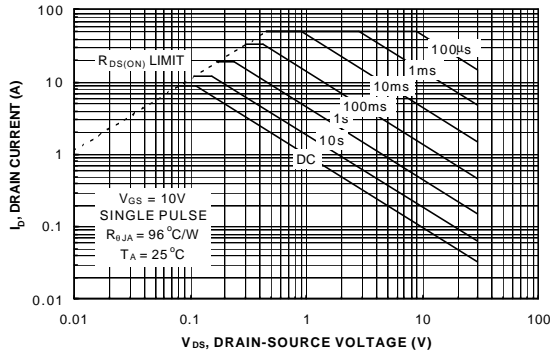


Figure 9. Maximum Safe Operating Area.

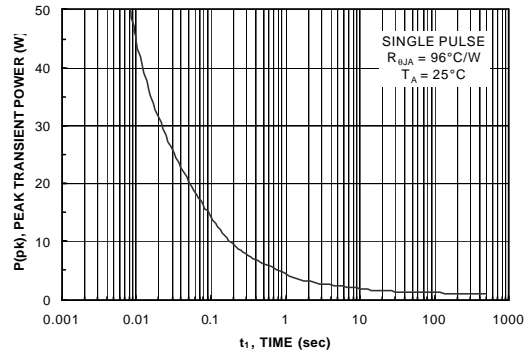


Figure 10. Single Pulse Maximum Power Dissipation.

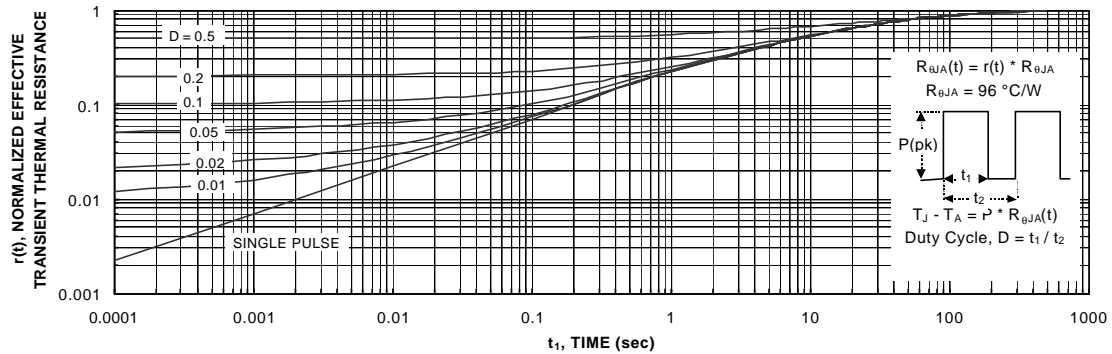


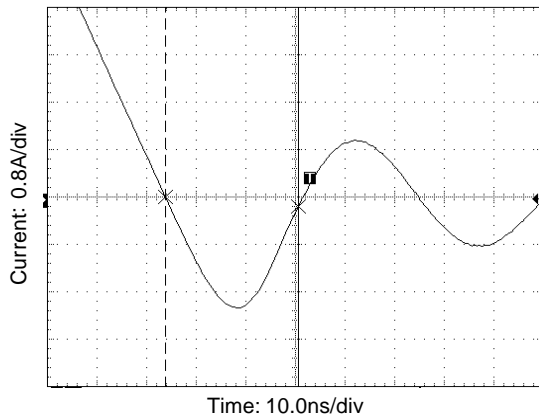
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

## Typical Characteristics (continued)

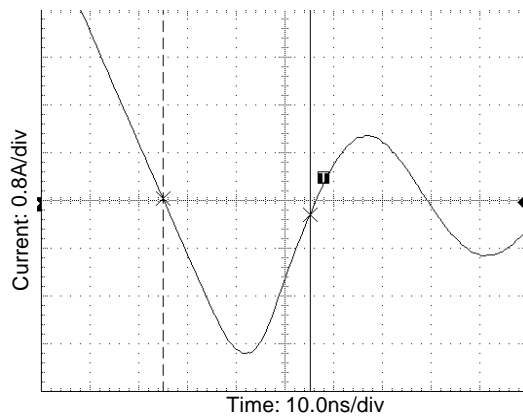
### SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDD6670S.



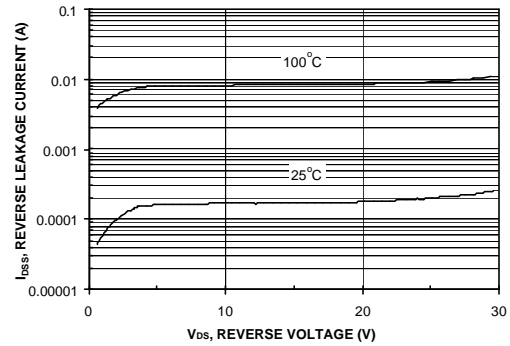
**Figure 12. FDD6670S SyncFET body diode reverse recovery characteristic.**

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDD6670A).



**Figure 13. Non-SyncFET (FDD6670A) body diode reverse recovery characteristic.**

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

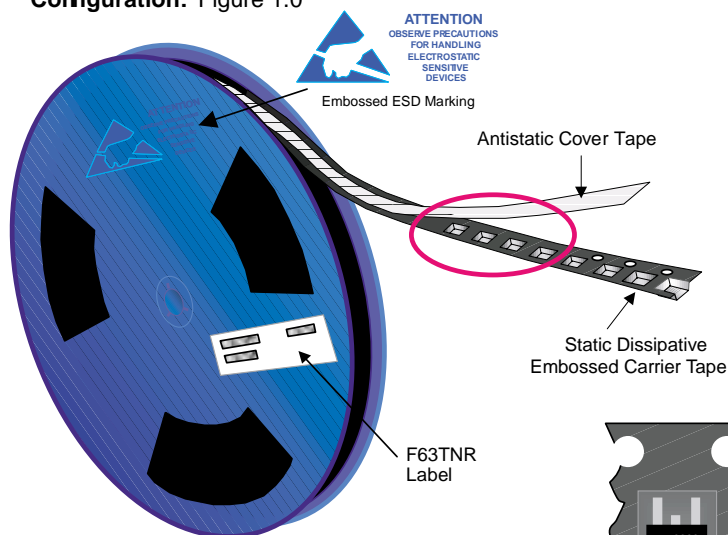


**Figure 14. SyncFET body diode reverse leakage versus drain-source voltage and temperature.**

# TO-252 (DPAK) Tape and Reel Data



## TO-252 (DPAK) Packaging Configuration: Figure 1.0

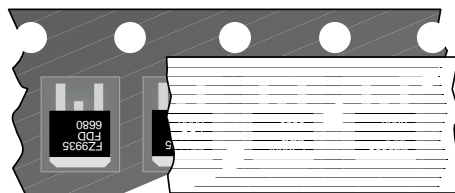


### Packaging Description:

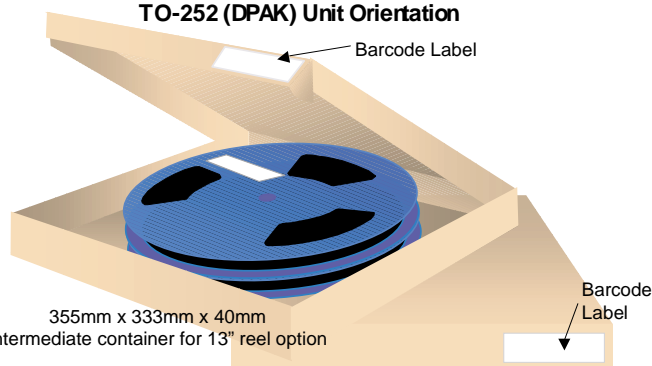
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film which comes either in HAA (Heat Activated Adhesive) or PSA (Pressure Sensitive Adhesive). HAA is primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. PSA is composed of transparent polyester backing film, pressure sensitive synthetic polymer (adhesive), and metallized transparent conductive polyester film on the inner face.

These reeled parts in standard option are shipped with 2500 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.



### TO-252 (DPAK) Unit Orientation

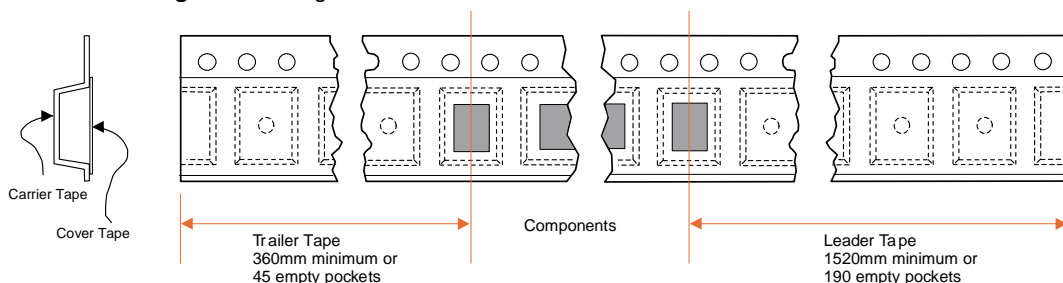


DPAK (TO-252) Packaging Information	
Packaging Option	Standard (no flow code)
Packaging type	TNR
Qty per Reel/Tube/Bag	2,500
Reel Size	13" Dia
Box Dimension(mm)	355x333x40
Max qty per Box	5,000
Weight per unit(gm)	0.300
Weight per Reel(kg)	1.200
Note/Comments	

### Barcode Label sample

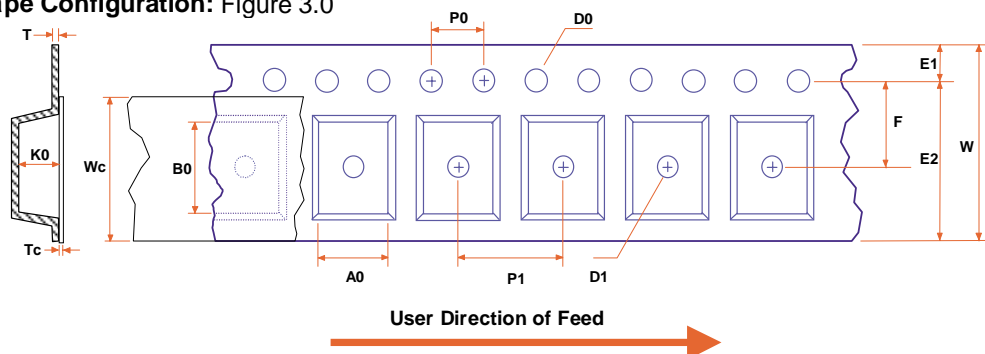
LOT: CBVK741B019	QTY: 2500
<b>CBVK741B019</b>	<b>3000</b>
PART ID: FDD6680	SPEC:
<b>FDD6680</b>	
D/C1: Z9942ab	QTY1: SPEC REV:
D/C2: QTY2: C/PN:	
FAIRCHILD SEMICONDUCTOR CORPORATION (F63TNR)	

## TO-252 (DPAK) Tape Leader and Trailer Configuration: Figure 2.0



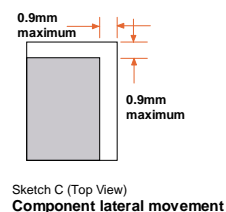
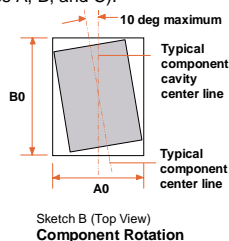
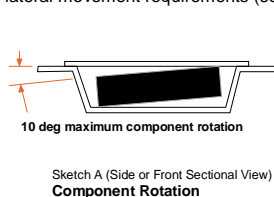
## TO-252 (DPAK) Tape and Reel Data, continued

### TO-252 (DPAK) Embossed Carrier Tape Configuration: Figure 3.0

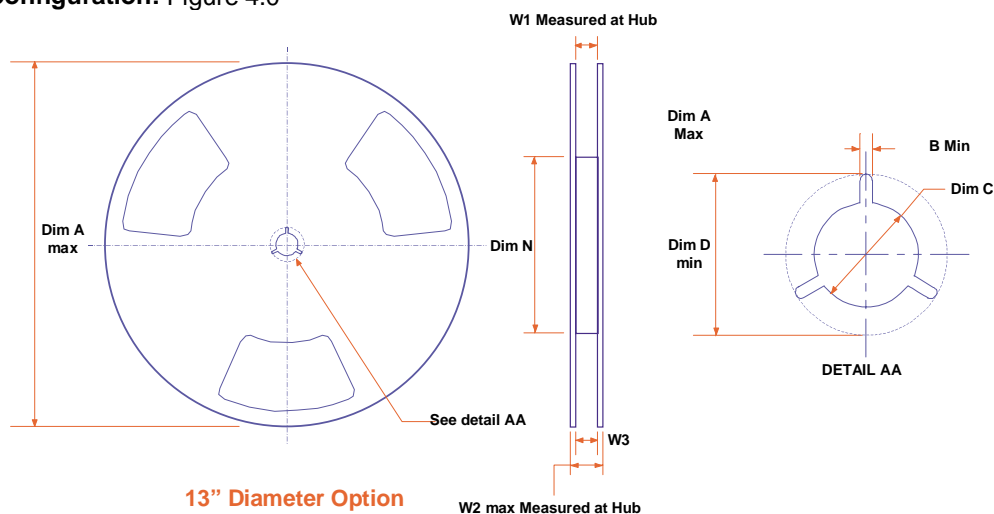


Dimensions are in millimeter														
Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
TO-252 (16mm)	6.90 +/-0.10	10.50 +/-0.10	16.0 +/-0.3	1.55 +/-0.05	1.5 +/-0.10	1.75 +/-0.10	14.25 min	7.50 +/-0.10	8.0 +/-0.1	4.0 +/-0.1	2.65 +/-0.10	0.30 +/-0.05	13.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



### TO-252 (DPAK) Reel Configuration: Figure 4.0



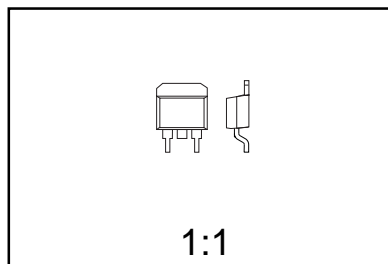
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
164mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.646 +0.078/-0.000 16.4 +2/0	0.882 22.4	0.626 - 0.764 15.9 - 19.4



# TO-252 Package Dimensions



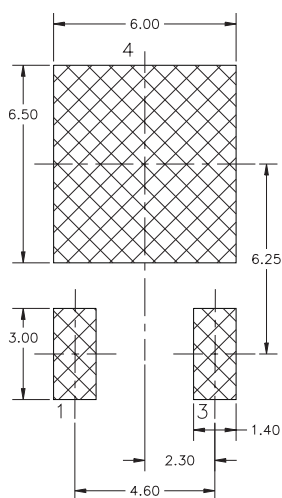
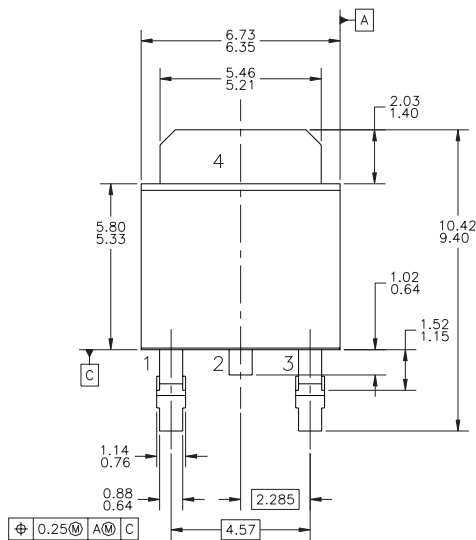
## TO-252 (FS PKG Code 36)



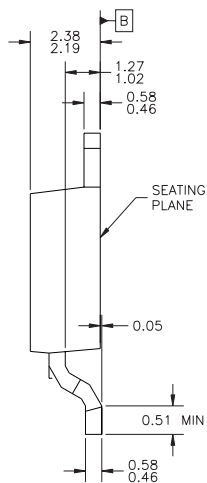
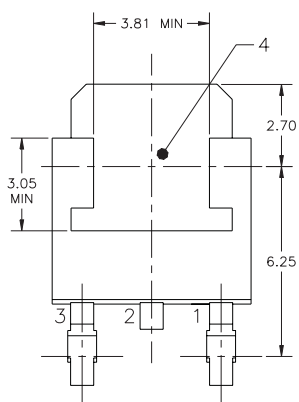
Scale 1:1 on letter size paper

Dimensions shown below are in:  
inches [millimeters]

Part Weight per unit (gram): 0.300



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.

B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE B, VARIATION AB, ITEM 10.268, DATED SEPTEMBER 1988.

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CoolFET™	FRFET™	PACMAN™	Stealth™	
CROSSVOLT™	GlobalOptoisolator™	POP™	SuperSOT™-3	
DenseTrench™	GTO™	Power247™	SuperSOT™-6	
DOMETM	HiSeC™	PowerTrench®	SuperSOT™-8	
EcoSPARK™	ISOPLANAR™	QFET™	SyncFET™	
E <sup>2</sup> CMOS™	LittleFET™	QST™	TinyLogic™	
EnSigna™	MicroFET™	QT Optoelectronics™	TruTranslation™	
FACT™	MicroPak™	Quiet Series™	UHC™	
FACT Quiet Series™	MICROWIRE™	SILENT SWITCHER®	UltraFET®	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.